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**Only the modified parts of the document are subject of the Public Review.**

**Other comments will be treated as additional Change Requests.**

*NOTE: The Word-file identifies all deletions and additions marked with revision tracking and comments stating the implemented Change Request. In the pdf-file all deletions were hidden.*

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**DISCLAIMER** (for drafts)

This document is an ECSS Draft Standard. It is subject to change without any notice and may not be referred to as an ECSS Standard until published as such.

**Foreword**

This Standard is one of the series of ECSS Standards intended to be applied together for the management, engineering, product assurance and sustainability in space projects and applications. ECSS is a cooperative effort of the European Space Agency, national space agencies and European industry associations for the purpose of developing and maintaining common standards. Requirements in this Standard are defined in terms of what shall be accomplished, rather than in terms of how to organize and perform the necessary work. This allows existing organizational structures and methods to be applied where they are effective, and for the structures and methods to evolve as necessary without rewriting the standards.

This Standard has been prepared and maintained under the authority of the Space Components Steering Board (SCSB) in partnership with the European Space Agency (ESA), national space agencies (NSAs) and the European space industry, reviewed by the ECSS Product Assurance Panel and approved by the ECSS Steering Board.

The end-of-life parameter drifts are not covered by this Standard.

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Change log

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Introduction

This Standard specifies derating requirements applicable to electronic, electrical and electromechanical components.

Derating is a long standing practice applied to components used on spacecrafts. Benefits of this practice are now proven, but for competitiveness reasons, it becomes necessary to find an optimized reliability. Too high a derating can lead to over-design, over-cost and over-sizing of components, the direct consequence being excess volume and weight. The aim is to obtain reliable and high performance equipment without over-sizing of the components. For this reason and if possible, this Standard provides derating requirements depending on mission duration and mean temperature, taking into account demonstrated limits of component capabilities.

# Scope

This Standard applies to all parties involved at all levels in the realization of space segment hardware and its interfaces.

The objective of this Standard is to provide customers with a guaranteed performance and reliability up to the equipment end-of-life. To this end, the following are specified:

* Load ratios or limits to reduce stress applied to components;
* Application rules and recommendations.

This standard may be tailored for the specific characteristics and constraints of a space project, in accordance with ECSS-S-ST-00.

# Normative references

The following normative documents contain provisions which, through reference in this text, constitute provisions of this ECSS Standard. For dated references, subsequent amendments to, or revisions of any of these publications do not apply. However, parties to agreements based on this ECSS Standard are encouraged to investigate the possibility of applying the most recent editions of the normative documents indicated below. For undated references the latest edition of the publication referred to applies.

|  |  |
| --- | --- |
| ECSS-S-ST-00-01 | ECSS system - Glossary of terms |
| ECSS-Q-ST-60 | Space product assurance - Electrical, electronic and electromechanical (EEE) components |
| ESCC 2269010 | Evaluation test programme for monolithic microwave integrated circuits (MMICS) |
| ESCC 2265010 | Evaluation Test Programme for Discrete Microwave Semiconductors |

# Terms, definitions and abbreviated terms

## Terms from other standards

1. For the purpose of this Standard, the terms and definitions from ECSS‑ST‑00‑01 apply.
   1. component
   2. derating
   3. performance

## Terms specific to the present standard

1. ambient temperature

temperature surrounding a component

1. bundle

set of two or more wires arranged in parallel ,tied or laced together.

1. case temperature

temperature on the component package surface

1. hot spot temperature

highest measured or predicted temperature within any component

1. junction temperature

highest measured or predicted temperature at the junction within a semiconductor or micro-electronic device

1. Predicted temperature can be taken as Tcase + thermal resistance between junction and case times actual power (Watt) of the device.
2. load ratio

permissible operating level after derating has been applied; given as a percentage of a parameter rating

1. operating conditions

parameter stress and environment (temperature, vibration, shock and radiation) in which components are expected to operate

1. RadPack

package designed to provide some form of radiation protection

1. rating

maximum parameter value specified and guaranteed by the component manufacturer and component procurement specification

1. Rating is considered as a limit not to be exceeded during operation and constitutes in most cases the reference for derating.
2. surge

strong rush or sweep

[Collins dictionary and thesaurus]

1. transient

brief change in the state of a system

[Collins dictionary and thesaurus]

## Abbreviated terms

For the purpose of this Standard, the abbreviated terms from ECSS‑S‑ST‑00‑01 and the following apply:

| Abbreviation | Meaning |
| --- | --- |
| A/D | analog to digital |
| ASIC | application specific integrated circuit |
| C | capacitance |
| DRAM | dynamic random access memory |
| EEPROM | electrical erasable programmable read only memory |
| EPROM | erasable programmable read only memory |
| ESCC | European Space Component Coordination |
| ESR | equivalent series resistance |
| f | frequency |
| FET | field effect transistor |
| GaAs | gallium arsenide |
| ISO | International Organization for Standardization |
| InP | indium posphide |
| LED | light emitting diode |
| MOS | metal on silicon |
| MIL (spec) | specification of the US Department of Defense |
| MMIC | monolithic microwave integrated circuit |
| NASA | National Aeronautics and Space Administration |
| P | power |
| PROM | programmable read only memory |
| RadHard | radiation hardened |
| Ri | insulation resistance |
| RF | radio-frequency |
| SEBO | single event burn-out |
| SEGR | single event gate rupture |
| Si, SiGe | silicon, silicon germanium |
| SOA | safe operating area |
| SRAM | static random access memory |
| Tj | junction temperature |
| Tjmax | absolute maximum rated junction temperature |
| Top | operating temperature |
| VCE | collector-emitter voltage |

# User responsibility

ECSS-Q-ST-30-11\_0140001

The user of this Standard shall verify that the ordered assurance level of procured components is compatible with the intended application.

# Derating

## Overview

The term derating refers to the intentional reduction of electrical, thermal and mechanical stresses on components to levels below their specified rating. Derating is a means of extending component life, increasing reliability and enhancing the end-of-life performance of equipment.

Derating participates in the protection of components from unexpected application anomalies and board design variations.

The load ratios or limits given in clause 6 were derived from information available at the time of writing this Standard and do not preclude further derating for specific applications.

This Standard also defines how to handle transients.

## Principles of derating

The component parameter strength defines the limits and the performance component technology in the particular application and varies from manufacturer to manufacturer, from type to type, and from lot to lot and can be represented by a statistical distribution. Likewise, component stress can be represented by a statistical distribution. Figure 5‑1 illustrates the strength of a component and the stress applied at a given time, where each characteristic is represented by a probability density function.

A component operates in a reliable way if its parameter strength exceeds the parameter stress. The designer should ensure that the stress applied does not exceed the component parameter strength. This is represented by the intersection (shaded area) in Figure 5‑1. The larger the shaded area, the higher the possibility of failure becomes.

There are two ways, which may be used simultaneously, in which the shaded area can be decreased:

* Decrease the stress applied (which moves the stress distribution to the left).
* Increase the component parameter strength (by selecting over-sized components) thereby moving the strength distribution to the right.

The goal is to minimize the stress-to-strength ratio of the component. Derating moves the parameter stress distribution to the left while the selection processes applied to the components for space applications contribute to moving the parameter strength distribution to the right. The selection processes also reduce the uncertainty associated with the component parameter strength.

Derating reduces the probability of failure, improves the end-of-life performance of components and provides additional design margins.

Another effect of derating is to provide a safety margin for design. It allows integrating parameter distribution from one component to another, and from one procurement to another.



Figure ‑: Parameter stress versus strength relationship

## Applicability and component selection

### Overview

This Standard applies to all components, selected for space applications, that are used for a significant duration. The meaning of “significant duration” is a period that contributes to the component life, for instance, one month is considered to be a significant duration. These requirements apply to screened components procured in accordance with approved space specifications.

This Standard only applies to approved components for which quality was proven after rigorous testing in accordance with ECSS-Q-ST-60.

Derating applies on normal operational conditions, where “normal” is opposed to “fault” and “Operational” indicates all functional modes of the unit.

Derating analysis is performed at the equipment maximum hot acceptance temperature, unless otherwise specified.

### Requirements

ECSS-Q-ST-30-11\_0140002

Derating shall be applied in consideration of temperature limits recommended by the manufacturer.

ECSS-Q-ST-30-11\_0140003

The derating requirements of this Standard shall not be used as a justification to upgrade the quality level of components.

ECSS-Q-ST-30-11\_0140004

The derating requirements shall be taken into account at the beginning of the design cycle of an equipment for any consequential design trade-off to be made..

1. It is important to pay specific attention to breadboards and engineering models where parameter derating was not considered.

ECSS-Q-ST-30-11\_0140005

For families and groups of components excluded from this Standard due to the lack of experimental data and failure history, the user shall consult a component design and reliability specialist to apply the requirements of this Standard.

ECSS-Q-ST-30-11\_0140006

Components may be excluded from this Standard if they are used for short durations of less than one month provided the device ratings are not exceeded, and it is ensured that the applied stress level does not exceed the component maximum rating.

1. For example, components used in solar generator deployment systems, redundancy commutation and launchers (except in some specific cases, noted family by family).

ECSS-Q-ST-30-11\_0140007

The derating requirements are not applicable to test conditions for which the maximum ratings shall not be exceeded.

1. For example, circuit or equipment level qualification and EMC.

ECSS-Q-ST-30-11\_0140008

Derating requirements are not applicable to fault conditions, for which the maximum rating shall not be exceeded, with the exception defined in 5.3.2h.

ECSS-Q-ST-30-11\_0140009

Where components are required to operate in protection mode or in fail-safe mode in order to prevent failure propagation, the components concerned shall meet the derating requirements and application rules when performing the protection or fail-safe function under the worst failure case.

1. 1 Short circuit is an example of failure propagation.
2. 2 Example of protection or fail-safe function under the worst failure case: highest stress applied to the components that can last throughout the mission.

### Requirements ESCC exceptions

ECSS-Q-ST-30-11\_0140010

For a particular type or manufacturer, when a specific derating rule is defined in the appendix of the approved ESCC detail specification issued by the ESCC Executive, it shall take precedence over the generic requirement of this standard.

ECSS-Q-ST-30-11\_0140011

Users shall check for application the actual status of the ESCC Derating exceptions on the following ESCC web site page: [ESCC Derating deviations](https://escies.org/webdocument/showArticle?id=825&groupid=6).

1. A list of the ESCC detail specifications applicable at the time of publication and containing deviations to general derating requirements of this standard is available in informative Annex B.

ECSS-Q-ST-30-11\_0140012

Users shall clearly identify in the Parts Stress Analysis document the list of the ESCC Derating exceptions taken into consideration in their analysis.

## Derating parameters

### Overview

Derating requirements are provided in clause 6 for each component family.

For each category, the parameters to be derated are identified. The main parameters to be derated are:

* junction or case temperature;
* power (rating, dissipation);
* voltage;
* current.

The parameters to be derated depend on component type.

A stress balancing concept offers flexibility between one stress versus another (voltage and temperature). In some cases, e.g. resistors, derating has a direct impact on component performance.

### Requirements for transient and surge conditions

ECSS-Q-ST-30-11\_0140013

For transient or surge conditions, if ratings are provided, the same derating figures as for steady-state equivalent parameters shall be used.

ECSS-Q-ST-30-11\_0140014

For transient or surge conditions, if ratings are not provided, then it shall be assured that the transient or surge values are below the steady-state specified maximum ratings.

ECSS-Q-ST-30-11\_0140015

For all periodic signals or transient conditions which are repeated or made incessant, the steady-state derating figures shall apply.

<<deleted>>

ECSS-Q-ST-30-11\_0140016

As an exception in case clause 5.4.2c is not compatible for specific repeated and incessant transient use conditions, for the parts types and parameters listed, load ratio shall not exceed the steady state derated values +10 % or 80 % of the steady state rated values, which ever is lower:

Connectors: voltage, current

Ceramic Capacitors: voltage

Resistors: current

Diodes: current

Transistors\_ bipolar , MOSFETs, power FETs: current.

## Additional rules and recommendations

### Overview

In addition to strict derating requirements, some application rules and recommendations are given in this Standard to achieve the suitable reliability. This additional application rules and recommendations are listed separately in the clauses titled “Additional requirements not related to derating”. This disposition is valid until other adequate ECSS documents can host these additional clauses.

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140017

Where radiation sensitive components are identified, the chosen component technologies and the mitigation factors, such as shielding, shall meet the customer’s requirement.

# Tables for load ratios or limits

## Overview

This clause provides the load ratios or limits.

They are also available on the World Wide Web at the following address:

https://escies.org

Abbreviations used in the tables are explained in clause 3.

Annex A contains a complete listing of the family and group codes for parts that are referred to in this Standard.

Annex B contains ESCC exceptions at date of publication of this standard.

## Capacitors: ceramic - family-group code: 01-01 and 01-02

### General

ECSS-Q-ST-30-11\_0140018

The capacitor stress sum value of steady-state voltage, AC voltage shall not exceed the load ratios specified hereunder. For transients refer to clause 5.4.

ECSS-Q-ST-30-11\_0140163

<<deleted>>

ECSS-Q-ST-30-11\_0140164

<<deleted>>

ECSS-Q-ST-30-11\_0140165

Internal heating due to ESR can increase ageing and should be taken into account by applying a margin in temperature.

Where ESR is not known at the frequency of a ripple current, an extrapolation of the ESR value and resonance, from manufacturer’s or test data, should be made where possible.

### Derating

ECSS-Q-ST-30-11\_0140020

Parameters of capacitors from family-group code 01-01 and 01-02 shall be derated as per Table 6‑1.

ECSS-Q-ST-30-11\_0140021

Table ‑: Derating of parameters for capacitors family-group code 01-01 and 01-02



### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140022

The dV/dt rating capability of the capacitors shall be respected.

## Capacitors: solid tantalum - family-group code: 01-03

### General

ECSS-Q-ST-30-11\_0140023

The capacitor stress sum value of steady-state voltage and AC voltage shall not exceed the load ratio specified hereunder, for transients refer to clause 5.4.

<<deleted - moved to 6.3.3a>>

ECSS-Q-ST-30-11\_0140024

Surge current shall be derated to 75 % of the Isurge max. Isurge max is defined as Vrated/(ESR+Rs). Vrated is the maximum rated voltage, ESR is the maximum specified value and Rs is the value of series resistance specified in the circuit for surge current testing as defined in the applicable procurement specification.

ECSS-Q-ST-30-11\_0140025

Reverse voltage shall not exceed 75 % of the manufacturer’s specified maximum value for the reverse voltage.

ECSS-Q-ST-30-11\_0140026

Ripple power shall never exceed 50 % of the manufacturer’s specified maximum value.

ECSS-Q-ST-30-11\_0140166

Internal heating due to ESR can increase ageing and should be taken into account by applying a margin in temperature.

Where ESR is not known at the frequency of a ripple current, an extrapolation of the ESR value and resonance, from manufacturer’s or test data, should be made where possible.

### Derating

ECSS-Q-ST-30-11\_0140027

Parameters of capacitors from family-group code 01-03 shall be derated as per Table 6‑2.

ECSS-Q-ST-30-11\_0140028

Table ‑: Derating of parameters for capacitors family-group code 01-03



### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140029

100 % surge current screening shall be applied for all surface mounted capacitors types.

ECSS-Q-ST-30-11\_0140030

The dV/dt rating capability of the capacitors shall be respected.

## Capacitors: non-solid tantalum - family-group code: 01-04

### General

ECSS-Q-ST-30-11\_0140031

Reverse voltage shall not exceed 75 % of the manufacturer’s specified maximum value for the reverse voltage.

ECSS-Q-ST-30-11\_0140032

Manufacturer’s ratings for ripple power or current shall never be exceeded.

ECSS-Q-ST-30-11\_0140167

Internal heating due to ESR can increase ageing and should be taken into account by applying a margin in temperature.

Where ESR is not known at the frequency of a ripple current, an extrapolation of the ESR value and resonance, from manufacturer’s or test data, should be made where possible.

### Derating

ECSS-Q-ST-30-11\_0140033

Parameters of capacitors from family-group code 01-04 shall be derated as per Table 6‑3.

ECSS-Q-ST-30-11\_0140034

Table ‑: Derating of parameters for capacitors family-group code



### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140035

<<deleted>>

## Capacitors: Plastic metallized - family-group code: 01-05

### General

<<deleted - modified and moved to clause 6.5.3>>

<<deleted>>

ECSS-Q-ST-30-11\_0140168

Internal heating due to ESR can increase ageing and should be taken into account by applying a margin in temperature.

Where ESR is not known at the frequency of a ripple current, an extrapolation of the ESR value and resonance, from manufacturer’s or test data, should be made where possible.

### Derating

ECSS-Q-ST-30-11\_0140036

Parameters of capacitors from family-group code 01-05 shall be derated as per Table 6‑4.

ECSS-Q-ST-30-11\_0140037

Table ‑: Derating of parameters for capacitors family-group code 01-05



### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140038

Self healing requirements (if applicable): clearing recommendations from manufacturers shall be followed.

ECSS-Q-ST-30-11\_0140039

The dV/dt rating capability of the capacitors shall be respected.

## Capacitors: glass and porcelain - family-group code: 01-06

### General

ECSS-Q-ST-30-11\_0140169

Internal heating due to ESR can increase ageing and should be taken into account by applying a margin in temperature.

Where ESR is not known at the frequency of a ripple current, an extrapolation of the ESR value and resonance, from manufacturer’s or test data, should be made where possible.

### Derating

ECSS-Q-ST-30-11\_0140040

Parameters of capacitors from family-group code 01-06 shall be derated as per Table 6‑5.

ECSS-Q-ST-30-11\_0140041

Table ‑: Derating of parameters for capacitors family-group code 01-06



### Additional requirements not related to derating

No additional requirement.

## Capacitors: mica and reconstituted mica - family-group code: 01-07

### General

ECSS-Q-ST-30-11\_0140170

Internal heating due to ESR can increase ageing and should be taken into account by applying a margin in temperature.

Where ESR is not known at the frequency of a ripple current, an extrapolation of the ESR value and resonance, from manufacturer’s or test data, should be made where possible.

### Derating

ECSS-Q-ST-30-11\_0140042

Parameters of capacitors from family-group code 01-07 shall be derated as per Table 6‑6.

ECSS-Q-ST-30-11\_0140043

Table ‑: Derating of parameters for capacitors family-group code 01-07



### Additional requirements not related to derating

No additional requirement.

## Capacitors: feedthrough - family-group code: 01-10

### General

ECSS-Q-ST-30-11\_0140171

Internal heating due to ESR can increase ageing and should be taken into account by applying a margin in temperature.

Where ESR is not known at the frequency of a ripple current, an extrapolation of the ESR value and resonance, from manufacturer’s or test data, should be made where possible.

### Derating

ECSS-Q-ST-30-11\_0140044

Parameters of capacitors from family-group code 01-10 shall be derated as per Table 6‑7.

ECSS-Q-ST-30-11\_0140045

Table ‑: Derating of parameters for capacitors family-group code 01-10



### Additional requirements not related to derating

No additional requirement.

## Capacitors: semiconductor technology (MOS type) - family-group code: 01-11

### General

ECSS-Q-ST-30-11\_0140172

Internal heating due to ESR can increase ageing and should be taken into account by applying a margin in temperature.

Where ESR is not known at the frequency of a ripple current, an extrapolation of the ESR value and resonance, from manufacturer’s or test data, should be made where possible.

### Derating

ECSS-Q-ST-30-11\_0140046

Parameters of capacitors from family-group code 01-11 shall be derated as per Table 6‑8.

ECSS-Q-ST-30-11\_0140047

Table ‑: Derating of parameters for capacitors family-group code 01-11



### Additional requirements not related to derating

No additional requirement.

## Capacitors: miscellaneous (variable capacitors) - family-group code: 01-99

### General

ECSS-Q-ST-30-11\_0140173

Internal heating due to ESR can increase ageing and should be taken into account by applying a margin in temperature.

Where ESR is not known at the frequency of a ripple current, an extrapolation of the ESR value and resonance, from manufacturer’s or test data, should be made where possible.

### Derating

ECSS-Q-ST-30-11\_0140048

Parameters of capacitors from family-group code 01-99 shall be derated as per Table 6‑9.

ECSS-Q-ST-30-11\_0140049

Table ‑: Derating of parameters for capacitors family-group code 01-99



### Additional requirements not related to derating

No additional requirement.

## Connectors - family-group code: 02-01, 02-02, 02-03, 02-07 and 02-09

### General

<<deleted - moved to 6.11.3a>>

<<deleted - moved to 6.11.3b>>

<<deleted - moved to 6.11.3c>>

<<deleted - moved to 6.11.3d>>

### Derating

ECSS-Q-ST-30-11\_0140050

Parameters of connectors from family-group code 02-01, 02-02, 02-03, 02-07 and 02-09 shall be derated as per Table 6‑10.

ECSS-Q-ST-30-11\_0140051

Table ‑: Derating of parameters for connectors family-group code 02-01, 02-02, 02-03, 02-07 and 02-09

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Working voltage | 25% of the connector Dielectric Withstanding test Voltage (at sea level, unconditioned)  - or –  75% of the connector rated operating (working) voltage (at sea level),  whichever is lower. |
| Current | 50 % |
| Maximum operating temperature | 30 °C below maximum rated temperature. |
| <<deleted>> | <<deleted - moved to 6.11.3e>> |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140052

For power connectors, power and return lines shall be separated by at least one unassigned contact to reduce the short-circuit risk.

ECSS-Q-ST-30-11\_0140053

Connector savers shall be used during testing of equipment to minimize number of mating and de-mating cycles.

ECSS-Q-ST-30-11\_0140054

When multi-pin connectors are close to one another, they shall be configured such that mating with a wrong connector is not possible or the contact assignments are chosen such that mating with a wrong connector does not cause damage to the unit itself nor to any other element of the system.

ECSS-Q-ST-30-11\_0140055

The connector and its constituent parts shall be from the same manufacturer.

ECSS-Q-ST-30-11\_0140056

Maximum mating and de-mating cycles shall be limited to 50 cycles.

## Connectors RF - family-group code: 02-05

### General

<<deleted - moved to 6.12.3a>>

### Derating

ECSS-Q-ST-30-11\_0140057

Parameters of connectors RF from family-group code 02-05 shall be derated as per Table 6‑11.

ECSS-Q-ST-30-11\_0140058

Table 6‑11: Derating of parameters for connectors RF family-group code 02-05

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| RF power | 25% of the connector Dielectric Withstanding test Voltage (at sea level, unconditioned)  - or –  75% of the connector rated operating (working) voltage (at sea level),  whichever is lower. |
| Working voltage | 50 % of specified voltage at any altitude (pin-to-pin and pin-to-shell). |
| Maximum operating temperature | 30 °C below maximum rated temperature. |
| <<deleted>> | <<deleted - moved to 6.12.3c>> |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140059

Connector savers shall be used during testing of equipment to minimize number of mating and demating cycles.

ECSS-Q-ST-30-11\_0140060

RF power shall be limited such that a 6 dB margin exists before the onset of multipactor.

ECSS-Q-ST-30-11\_0140061

Maximum mating and de-mating cycles shall be limited to 50 cycles.

## Piezo-electric devices: crystal resonator - family-group code: 03-01

### General

No general clause.

### Derating

ECSS-Q-ST-30-11\_0140062

Parameters of piezo-electric devices from family-group 03-01 shall be derated as per Table 6‑12.

ECSS-Q-ST-30-11\_0140063

Table ‑: Derating of parameters for piezo-electric devices family-group code 03-01

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Drive level | 25 % power rated drive level (superseded by manufacturer required minimum drive level if not compatible). |

### Additional requirements not related to derating

No additional requirement.

## Diodes - family-group code: 04-01, 04-02, 04-03, 04-04, 04-06, 04-08, 04-10 and 04-14

### General

<<deleted - moved to 6.14.3a and 6.14.3b>>

### Derating

#### Diode (signal/switching, rectifier, including Schottky, pin derating table

ECSS-Q-ST-30-11\_0140064

Parameters of Diode (signal/switching, rectifier including Schottky, pin) shall be derated as per Table 6‑13.

ECSS-Q-ST-30-11\_0140065

Table ‑: Derating of parameters for Diode (signal/switching, rectifier including Schottky, pin)

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
|
| Forward current (IF): | 75% |
| Reverse voltage (VR) | 75 % |
| Dissipated power (PD) | 50 % (only if dissipated power is defined by the manufacturer) |
| Junction temperature (Tj ) | 110 °C or Tj max - 40 °C (whichever is lower) for Si devices.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax |

#### Diode (Zener, reference, transient suppression) derating table

ECSS-Q-ST-30-11\_0140066

Parameters of Diode (Zener, reference, transient suppression) shall be derated as per Table 6‑14.

ECSS-Q-ST-30-11\_0140067

Table ‑: Derating of parameters for Diode (Zener, reference, transient suppression)

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
|
| <<deleted>> | <<deleted>> |
| Dissipated power (PD)  or Current (IZM) | 65 % |
| Junction temperature (Tj ) | 110 °C or Tj max - 40 °C (whichever is lower) for Si devices.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140068

Diodes that can be radiation sensitive shall be:

recorded in the design file, and

the component selection be reviewed and approved as specified in ECSS-Q-ST-60.

ECSS-Q-ST-30-11\_0140174

Where power cycling is critical this should be considered.

ECSS-Q-ST-30-11\_0140069

The dV/dt rating capability of the diodes shall be respected.

## Diodes: RF/microwave - family-group code: 04-05, 04-11 to 04-13, 04-15, 04-16 and 04‑17

### General

<<deleted - moved to 6.15.3a.>>

### Derating

ECSS-Q-ST-30-11\_0140070

Parameters of Diodes from family-group code 04-05, 04-11 to 04-13, 04-15, 04-16 and 04‑17 shall be derated as per Table 6‑15.

ECSS-Q-ST-30-11\_0140071

Table ‑: Derating of parameters for Diodes family-group code 04-05, 04-11 to 04-13, 04-15, 04-16 and 04‑17

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Forward current | 50 % |
| Reverse voltage (VR) | 75 % |
| Dissipated power (PD) | 65 % |
| Junction temperature (Tj ) | 110 °C or Tj max - 40 °C (whichever is lower) for Si devices.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax |
| NOTE 1: Forward current is not applicable to varactors.  NOTE 2: Reverse voltage is not applicable to Gunn diodes. | |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140072

Diodes that can be radiation sensitive shall be:

recorded in the design file, and

the component selection be reviewed and approved as specified in ECSS-Q-ST-60.

## Feedthrough filters - family-group code: 05-01

### General

No general clause.

### Derating

ECSS-Q-ST-30-11\_0140073

Parameters of Feedthrough filters from family-group code 05-01 shall be derated as per Table 6‑16.

ECSS-Q-ST-30-11\_0140074

Table ‑: Derating of parameters for Feedthrough filters family-group code 05-01



### Additional requirements not related to derating

No additional requirement.

## Fuses: Cermet (metal film on ceramic) - family-group code: 06-01

### General

ECSS-Q-ST-30-11\_0140075

<<first sentence of requirement deleted - moved to 6.17.3a>>The derating requirements in 6.17.2 (below) are only applicable to Cermet types. The application and the deratings of other fuse technologies shall be justified.

<<deleted - moved to 6.17.3b>>

<<deleted - moved to 6.17.3c>>

### Derating

ECSS-Q-ST-30-11\_0140076

Parameters of Fuses from family-group code 06-01 shall be derated as per Table 6‑17.

ECSS-Q-ST-30-11\_0140077

Table ‑: Derating of parameters for Fuses family-group code 06-01



### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140078

Fuses shall be avoided whenever possible.

ECSS-Q-ST-30-11\_0140079

The largest fuse rating compatible with the source capability shall be used.

ECSS-Q-ST-30-11\_0140080

The power supply shall be capable of delivering three times the specified fuse rated current in order to obtain short fusing times.

## Inductors and transformers - family-group code: 07-01 to 07-03 and 14-01

### General

<<deleted - moved to 6.18.3a.>>

### Derating

ECSS-Q-ST-30-11\_0140081

Parameters of Inductors and transformers from family-group code: 07-01 to 07-03 and 14-01 shall be derated as per Table 6‑18.

ECSS-Q-ST-30-11\_0140082

Table ‑: Derating of parameters for Inductors and transformers family-group code 07-01 to 07-03 and 14-01

|  |  |  |
| --- | --- | --- |
| Parameters | Load ratio or limit | Special conditions |
| Maximum operating voltage (1) | 50 % of the applied insulation test voltage (2) | (1) Between winding-winding and between windings-case. The maximum operating voltage shall include DC, AC peak or combined.  (2) <<deleted - moved to 6.18.3b>> |
| Hot spot temperature | 20 °C below maximum rated temperature of any material used. |  |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140083

For custom-made inductors and transformers, the maximum rated temperature shall be evaluated taking into consideration the temperature characteristics of the materials used.

ECSS-Q-ST-30-11\_0140084

Unless specified in the procurement specification, the minimum insulation test voltage applied shall be 500 V.

For operating voltages greater than 200 V the insulation test voltage shall be equal to the partial discharge voltage (VPD), defined as the component qualification test level, where the partial discharge activity is detected, and with a test equipment sensitivity of no less than 1 pC.

## Integrated circuits: logic - family-group code: 08-10, 08-20, 08-21, 08-29 to 08-42, and 08-80

### General

<<deleted - moved to 6.19.3a>>

### Derating

ECSS-Q-ST-30-11\_0140085

Parameters of Integrated circuits from family-group code: 08-10, 08-20, 08-21, 08-29 to 08-42, and 08-80 shall be derated as per Table 6‑19.

ECSS-Q-ST-30-11\_0140086

Table ‑: Derating of parameters for Integrated circuits family-group code: 08-10, 08-20, 08-21, 08-29 to 08-42, and 08-80

|  |  |  |
| --- | --- | --- |
| Parameters | Load ratio or limit | Special conditions |
| Supply voltage (VCC) | Maximum manufacturer recommended value | **Supply voltage**  - Turn on transient peaks or other peaks shall not exceed the maximum rating.  - The input voltage shall not exceed the supply voltage (unless otherwise stated in the device specification). |
| Output current (Iout) | 80 % |  |
| Junction temperature (Tj ) | 110 °C or Tj max - 40 °C (whichever is lower) for Si devices.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax | <<deleted>> |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140087

Devices that can be radiation sensitive shall be recorded and approved in accordance with ECSS-Q-ST-60.

## Integrated circuits: non-volatile memories - family-group code: 08-22, 08-23 and 08-24

### General

<<deleted - moved to 6.20.3a>>

### Derating

ECSS-Q-ST-30-11\_0140088

Parameters of Integrated circuits from family-group code: 08-22, 08-23 and 08-24 shall be derated as per Table 6‑20.

ECSS-Q-ST-30-11\_0140089

Table ‑: Derating of parameters for Integrated circuits family-group code: 08-22, 08-23 and 08-24

|  |  |  |
| --- | --- | --- |
| Parameters | Load ratio or limit | Special conditions |
| Supply voltage (VCC) | Maximum manufacturer recommended value | **Supply voltage**  - Turn on transient peaks or other peaks shall not exceed the maximum rating.  - The input voltage shall not exceed the supply voltage (except adapted component design). |
| Output current (Iout) | 80 % |  |
| Maximum junction temperature (Tj max) | 110 °C or Tj max - 40 °C (whichever is lower) for Si devices.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax | <<deleted>> |
| Endurance and data retention |  | **Endurance**  The endurance (number of write and erase cycles) and the retention time-to-failure of EPROM, EEPROM and Flash devices can be derated from the manufacturer specification case by case. An acceleration model, such as Arrhenius’s law with an activation energy of 0,6 eV, or lower, shall be used to determine the equivalent time for space flight. |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140090

Devices that can be radiation sensitive shall be recorded and approved in accordance with ECSS-Q-ST-60.

## Integrated circuits: linear - family-group code: 08-50 to 08-60 and 08-69

### General

<<deleted - moved to 6.21.1a.>>

<<deleted - moved to 6.21.1b.>>

### Derating

ECSS-Q-ST-30-11\_0140091

Parameters of Integrated circuits from family-group code 08-50 to 08-60 and 08-69 shall be derated as per Table 6‑21.

ECSS-Q-ST-30-11\_0140092

Table ‑: Derating of parameters for Integrated circuits family-group code 08-50 to 08-60 and 08-69

|  |  |  |
| --- | --- | --- |
| Parameters | Load ratio or limit | Special conditions |
| Supply voltage (VCC) | 90 % of the maximum rated value | Supply voltage shall include DC + AC ripple. |
| Input voltage (VIN) or Input current (IIN) | For operational amplifiers:  Max rated of VIN (or 50 % on the input current)  For comparators:  100 % or derated circuit supply  voltage, whichever is lower,  For rail to tail amplifiers:  100 % or derated circuit supply voltage, whichever is lower .  For regulators: 90 % |  |
| Output current (Iout) | 80 % |  |
| Transients | Shall not exceed the specified maximum ratings. |  |
| Maximum junction temperature (Tj max) | 110 °C or Tj max - 40 °C, whichever is lower for Si devices.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax. |  |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140093

Linear circuits that can be radiation sensitive shall be:

recorded in the design file, and

the component selection be reviewed and approved as specified in ECSS-Q-ST-60.

ECSS-Q-ST-30-11\_0140175

Additional margins can be applied for radiation effects.

## Integrated circuits: linear converters - family-group code: 08-61 and 08-62

### General

<<deleted - moved to6.22.3a.>>

### Derating

ECSS-Q-ST-30-11\_0140095

Parameters of Integrated circuits from family-group code 08-61 and 08-62shall be derated as per Table 6‑22.

ECSS-Q-ST-30-11\_0140096

Table ‑: Derating of parameters for Integrated circuits family-group code 08-61 and 08-62

|  |  |  |
| --- | --- | --- |
| Parameters | Load ratio or limit | Special conditions |
| Junction temperature (Tj ) | 110 °C or Tj max - 40 °C, whichever is lower, for Si devices.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax. |  |
| Supply voltage (VCC) | 90 % | Supply voltage shall include DC + AC ripple. |
| Input voltage (VIN) | 100 % or derated circuit supply voltage, whichever is less. |  |
| Output current (Iout) | 80 % (D/A converters only) |  |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140097

Linear circuits that can be radiation sensitive shall be:

recorded in the design file, and

the component selection be reviewed and approved as specified in ECSS-Q-ST-60.

## Integrated circuits: MMICs - family-group code: 08-95

### General

<<deleted - moved to 6.23.3a.>>

### Derating

ECSS-Q-ST-30-11\_0140098

Each discrete cell constituting analogue custom MMICs shall be derated in accordance with this document’s requirements for the applicable family.

1. Discrete cells are for example: capacitors, resistors, diodes and transistors.

ECSS-Q-ST-30-11\_0140099

When operational reliability data is available, the compression level shall be derated to 2 dB under the highest compression level showing no drift.

MMICs having no compression data shall not be submitted to more than 1 dB of compression.

For digital cells, the derating rules applicable to integrated circuits shall be applied.

Parameters of custom designed MMICs shall be derated as per Table 6‑38.

Parameters of non-custom MMICs shall be derated as per Table 6‑23

Table 6‑23:Derating of parameters for non-custom MMICs

|  |  |
| --- | --- |
| Parameter | Load Ratio or Limit |
| Ipositive\_supply\_current | 75% |
| Inegative \_supply\_current | 75% |
| Vpositive\_supply | 80% for analog; max recommended value for digital |
| Vnegative supply | 80% for analog; min recommended value for digital |
| Vin\_dig\_max (max input digital command) | Less than or equal to Vpos (applied Vpositive\_supply) |
| Vin\_dig\_min (min input digital command) | 100% |
| Power dissipation | 80% |
| Tj\_max | Same rules as defined for transistors depending on the relevant technology |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140100

MMICs that can be radiation sensitive shall be chosen based on suitability and application.

Selection and use of MMICs specified in 6.23.3a shall be in accordance with ECSS-Q-ST-60 and this Standard.

## Integrated circuits: miscellaneous - family-group code: 08-99

### General

<<deleted - modified and moved to 6.24.2a>>

<< deleted - moved to 6.24.3a>>

### Derating

ECSS-Q-ST-30-11\_0140101

For all ICs not considered in the previous subgroups, the following derating rules shall be followed:

Manufacturer’s derating values.

Junction temperature: 110 °C or Tj max - 40 °C, whichever is lower.

For the part of the IC similar to logic ICs, apply the derating rules for logic subgroups, for the part similar to linear ICs, apply the derating rules for linear subgroups and so forth.

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140102

Integrated circuits that can be radiation sensitive shall be

recorded in a design file, and

the component selection be reviewed and approved as specified in ECSS-Q-ST-60.

## Relays and switches - family-group code: 09-01, 09‑02 and 16-01

### General

ECSS-Q-ST-30-11\_0140103

<<deleted, modified and moved to 6.25.1h and 6.25.1i>>

**ECSS-Q-ST-30-11\_0140104**

The minimum coil pulse duration for latching relays shall be 3 times the latch time (tL) or 40 ms, whichever is greater.

<<deleted - moved to 6.25.3a>>

ECSS-Q-ST-30-11\_0140105

Rated contact load voltage shall not be exceeded..

1. Voltage application has a strong impact on the contact current.

<<deleted - moved to 6.25.3b>>

<<deleted - moved to 6.25.3c.>>

<<deleted - moved to 6.25.3d.>>

The coil supply voltage shall be within the specified voltage range or between the specified rated and the maximum coil voltage.

When no minimum coil voltage is provided, the coil voltage shall be between 110 % of the maximum latch or reset or pick-up voltage over the full temperature range and the maximum coil voltage.

1. Latch or reset voltage are specified for latching device, pick-up voltage is specified for non-latching devices.

### Derating

ECSS-Q-ST-30-11\_0140106

Parameters of Relays and switches from family-group code 09-01, 09‑02 and 16-01 shall be derated as per Table 6‑24.

ECSS-Q-ST-30-11\_0140107

Table ‑: Derating of parameters for Relays and switches family-group code 09-01, 09‑02 and 16-01

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Contact current   * Resistive load |  |
|  | Number of operations less than 100 (including integrating and testing)   * When the specified overload current is rated at twice the rated contact current, the rated contact current may be used. * When the specified overload current is rated at 4 times the rated contact current, twice the rated contact current may be used. |
| * Inductive load | 50 % of inductive load if specified, or 40 % of resistive load otherwise. If an arc suppressor or snubber system is used, the load factor for resistive load may be applied. |
| * Motor load | 50 % of motor load if specified, or 20 % of resistive load otherwise |
| * Filament load | 10 % of resistive load. |
| Minimum contact current | * For rated contract current (ICR) ≤ 1 A, no limit needs to be considered. * For 1 A < ICR  ≤ 5 A, the current shall be greater than 10 mA. * For ICR  > 5 A, the current shall be greater than 10 % of the rated current. |
| Surge contact current (ISCR) | When the surge duration ≤ 10 μs, the surge contact current shall not exceed 4 times the rated contact current.  For surge duration > 10μs :    where:  *I* = Surge current  *Ir* = Rated current  *tp* = Surge duration |
| NOTE Current derating does not apply to contacts that only carry current and do not switch it or to contacts that switch at zero current. In the latter case, the number of operations is limited to the qualified number of operations. | |

### Additional requirements not related to derating

<<deleted and moved as NOTE to Table 6‑24>>

ECSS-Q-ST-30-11\_0140109

<<deleted, modified and moved to 6.25.3e and 6.25.3f>>

ECSS-Q-ST-30-11\_0140110

<<deleted, modified and moved to 6.25.3g and 6.25.3h>>

ECSS-Q-ST-30-11\_0140111

Suppression diodes shall not be used inside relays.

A double throw contact shall not be used to switch a load, movable contact, between a power supply and ground, stationary contacts.

A double throw contact may be accepted under the following conditions:

when switching off the power supply the other stationary contact is not connected to ground, or

the potential difference between stationary contacts is less than 10 V and the switched current less than 0,1 A.

Paralleled relays shall not be used to increase current switching capabilities of contacts.

When relays are paralleled for redundancy, in order to increase the system’s reliability, the sum of the paralleled currents shall not exceed the contact current rating.

## Resistors - family-group code: 10-01 to 10-11

### General

No general clause.

#### <<deleted>>

<<deleted - moved as Note to derating tables Table 6‑25 to Table 6‑31>>

<<6.26.1.2 to 6.26.1.7 deleted - modified and moved to 6.26.2.1 to 6.26.2.7>>

<<6.26.1.8 to 6.26.1.10 deleted>>

### Derating

<<deleted - moved to 6.26.2.8a including the derating table>>

#### Metal film precision resistor (type RNC, except RNC 90) derating table

ECSS-Q-ST-30-11\_0140112

Parameters of Metal film precision resistor (type RNC, except RNC 90) shall be derated as per Table 6‑25.

ECSS-Q-ST-30-11\_0140113

Table ‑: Derating of parameters for Metal film precision resistor (type RNC, except RNC 90)

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Voltage | 80 % |
| rms Power | 50 % up to 125 °C and further decreasing to 0 % at 150 °C |
| NOTE: The mentioned temperatures cited refer to case temperatures. | |

#### Metal film semi-precision resistor (type RLR) derating table

ECSS-Q-ST-30-11\_0140114

Parameters of Metal film semi-precision resistor (type RLR) shall be derated as per Table 6‑26.

ECSS-Q-ST-30-11\_0140115

Table ‑: Derating of parameters for Metal film semi-precision resistor (type RLR)

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Voltage | 80 % |
| rms Power | 50 % up to 70 °C and further decreasing to 0 % at 125 °C |
| NOTE: The mentioned temperatures cited refer to case temperatures. | |

#### Foil resistor (type RNC 90) derating table

ECSS-Q-ST-30-11\_0140116

Parameters of Foil resistor (type RNC 90) shall be derated as per Table 6‑27.

ECSS-Q-ST-30-11\_0140117

Table ‑: Derating of parameters for Foil resistor (type RNC 90)

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Voltage | 80 % |
| rms Power | 50 % up to 70 °C and further decreasing to 0 % at 125 °C |
| NOTE: The mentioned temperatures cited refer to case temperatures. | |

#### Wire-wound high precision resistor (type RBR 56) derating table

ECSS-Q-ST-30-11\_0140118

Parameters of Wire-wound high precision resistor (type RBR 56) shall be derated as per Table 6‑28.

ECSS-Q-ST-30-11\_0140119

Table ‑: Derating of parameters Wire-wound high precision resistor (type RBR 56)

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Voltage | 80 % |
| rms Power (type RBR 56) | Wire-wound for all tolerances: 50 % up to 115 °C, decreasing to 0 % at 130 °C |
| NOTE: The mentioned temperatures cited refer to case temperatures. | |

#### Wire-wound power resistor (type RWR, RER) derating table

ECSS-Q-ST-30-11\_0140120

Parameters of Wire-wound power resistor (type RWR, RER) shall be derated as per Table 6‑29.

ECSS-Q-ST-30-11\_0140121

Table ‑: Derating of parameters for Wire-wound power resistor (type RWR, RER)

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Voltage | 80 % |
| rms Power | 60 % up to 25 °C, decreasing to 0 % at 175 °C |
| NOTE: The mentioned temperatures cited refer to case temperatures. | |

#### Chip resistor (RM), network resistor derating table

ECSS-Q-ST-30-11\_0140122

Parameters of Chip resistor (RM), network resistor shall be derated as per Table 6‑30.

ECSS-Q-ST-30-11\_0140123

Table ‑: Derating of parameters for Chip resistor (RM), network resistor

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Voltage | 80 % |
| rms Power | 50 % up to 85 °C, decreasing to 0 % at 125 °C |
| NOTE: The mentioned temperatures cited refer to case temperatures. | |

#### Carbon composition resistor table

ECSS-Q-ST-30-11\_0140124

Parameters of Carbon composition resistor shall be derated as per Table 6‑31.

ECSS-Q-ST-30-11\_0140125

Table ‑: Derating of parameters for Carbon composition resistor

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Voltage | 80 % |
| rms Power | 50 % up to 70 °C, decreasing to 0 % at 100°C |
| NOTE: The mentioned temperatures cited refer to case temperatures. | |

#### Heaters

ECSS-Q-ST-30-11\_0140126

Actual rated power shall be specified in the applicable heater design drawing and be determined from the specified heating area (s) in cm2 taking into account the thermal properties of the mounted heater in the application.

ECSS-Q-ST-30-11\_0140127

Parameters of heaters shall be derated as per Table 6‑32.

ECSS-Q-ST-30-11\_0140128

Table ‑: Derating of parameters for Heaters

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Temperature(°C) | Foil heaters:  50 °C below the heater max rated temperature, or 30 °C below the adhesive max rated temperature for heater delivered with adhesive, whichever is lower. |
| Power density | Glued heaters:  Rated Power Density with heater suspended in still air defined in the specification |

#### Thick Film Power

Parameter of Thick Film Power from family group code 10-06 shall be derated as per Table 6‑33

Table 6‑33: Derating of parameters for Thick Film Power

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Voltage | 80% |
| Rated power (W) | Power : 60% up to 25°C. Decreasing to 0% at Tmax |

### Additional requirements not related to derating

No additional requirement.

## Thermistors - family-group code: 11-01 to 11-03

### General

No general clause.

### Derating

ECSS-Q-ST-30-11\_0140129

Parameters of Thermistors from family-group code 11-01 to 11-03 shall be derated as per Table 6‑34.

ECSS-Q-ST-30-11\_0140130

Table ‑: Derating of parameters for Thermistors family-group code 11-01 to 11-03

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Power | 50 % of the maximum power |

### Additional requirements not related to derating

No additional requirement.

## Transistors: bipolar - family-group code: 12-01 to 12-04 and 12-09

### General

<<deleted - moved to 6.28.3a>>

### Derating

ECSS-Q-ST-30-11\_0140131

Parameters of Transistors from family-group code 12-01 to 12-04 and 12-09 shall be derated as per Table 6‑35.

ECSS-Q-ST-30-11\_0140132

Table 6‑35: Derating of parameters for Transistors family-group code 12-01 to 12-04 and 12-09

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Collector-emitter voltage (VCE0) | 75 % |
| Collector-base voltage (VCB0) | 75 % |
| Emitter-base voltage (VEB0) | 75 % |
| Collector current (IC max) | 75 % |
| Base current (IB max), if specified | 75 % |
| Power (PD) | 65 % of maximum power |
| Junction temperature (Tj ) | 110 °C or Tj max - 40 °C (whichever is lower) for Si devices.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax. |
| <<Notes deleted and moved to 6.28.3b and 6.28.3c>> | |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140133

Transistors that can be radiation sensitiveshall be:

recorded in the design file, and

the component selection be reviewed and approved as specified in ECSS-Q-ST-60.

ECSS-Q-ST-30-11\_0140176

The safe-operating area when specified shall be respected.

ECSS-Q-ST-30-11\_0140177

In applications where power cycling is critical, the effects of power cycling shall be verified by analysis or test.

## Transistors: FET - family-group code: 12-05 and 12-06

### General

<<deleted - moved to 6.29.3a>>

<<deleted - moved to 6.29.3b>>

### Derating

ECSS-Q-ST-30-11\_0140134

Parameters of Transistors from family-group code 12-05 and 12-06 shall be derated as per Table 6‑36.

ECSS-Q-ST-30-11\_0140135

Table 6‑36: Derating of parameters for Transistors family-group code 12-05 and 12-06

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Drain to source voltage (VDS) | Drain to source voltage (VDS) 80 % of rated, or 80% of the SEE safe operating area (VDS versus VGS), whichever is lower.  If SEE Safe Operating Area was determined in accordance with ESCC 25100 then further derating of the SEE determined VDS is not required. |
| Gate to source voltage (VGS) | 75% of rated,  or  the SEE safe operating area (VDS versus VGS), whichever is lower  If SEE Safe Operating Area was determined in accordance with ESCC 25100 then further derating of the SEE determined VGS is not required. |
| Drain current (IDS) | 75 % |
| Power dissipation (PD) max | 65 % max |
| Junction temperature (Tj ) | 110 °C or Tj max - 40 °C (whichever is lower) for Si devices.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140136

Only SEE radiation characterized MOSFETs shall be used in space applications.

ECSS-Q-ST-30-11\_0140178

In applications where power cycling is critical, the effects of power cycling shall be verified by analysis or test.

## Transistors: RF: bipolar - family-group code: 12-10 and 12-13

### General

<<deleted - moved to 6.30.3a.>>

### Derating

ECSS-Q-ST-30-11\_0140137

Parameters of Transistors from family-group code 12-10 and 12-13 shall be derated as per Table 6‑37.

ECSS-Q-ST-30-11\_0140138

Table 6‑37: Derating of parameters for Transistors family-group code 12-10 and 12-13

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Collector-emitter voltage (VCE) | 75 % |
| Collector-base voltage (VCB) | 75 % |
| Emitter-base voltage (VEB) | 75 % |
| Collector current (IC) | 75 % |
| Base current (IB), if specified | 75 % |
| Power dissipation (PD) | 65 % or limited by the derating on operating temperature. |
| Junction temperature (Tj ) | 110 °C or Tj max - 40 °C (whichever is lower) for Si and SiGe bipolar transistors.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax.  115 °C or Tj max - 25°C (whichever is lower) for GaAs and InP bipolar transistors.  ESCC Exception:  125 °C for GaAs or InP, providing   1. # that the specified maximum rating Tmax ≥ 150 °C , 2. # that Devices or Processes are supported by ESCC 2269010 and 2265010 evaluation program or equivalent 3. # that the related evaluation reports are available |
| NOTE | |

When not supported by reliability data, compression levels shall not exceed 1 dB.

When supported by reliability data, the RF input power shall be derated by 2 dB back off from the highest level showing no drift.

In the case when the transistor is specified through a maximum RF input power, the RF input power shall be derated by 3 dB back off from the specified RF input power.

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140139

Transistors that can be radiation sensitiveshall be :

recorded in the design file, and

the component selection be reviewed and approved a specified in ECSS-Q-ST-60.

## Transistors: RF: FET - family-group code: 12-12, 12-14, 12-15(FET) and 12-16(FET)

### General

<<deleted - moved to 6.31.3a.>>

### Derating

ECSS-Q-ST-30-11\_0140140

Parameters of Transistors from family-group code 12-12, 12-14, 12-15(FET) and 12-16(FET) shall be derated as per Table 6‑38.

Parameters of custom designed MMICs shall be derated as per Table 6‑38.

When not supported by reliability data, compression levels shall not exceed 1 dB.

When supported by reliability data, the RF input power shall be derated by 2 dB back off from the highest level showing no drift.

In the case when the transistor is specified through a maximum RF input power, the RF input power shall be derated by 3dB back off from the specified RF input power.

ECSS-Q-ST-30-11\_0140141

Table 6‑38: Derating of parameters for Transistors family-group code 12-12, 12-14, 12-15(FET) and 12-16(FET)

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Drain to source voltage (VDS) | 75 % |
| Gate to source voltage (VGS) | 75 % |
| Gate to drain voltage (VGD) | 75 % |
| Drain current (IDS) | 75 % |
| Power dissipation (PD) | 80 % or limited by the derating on operating temperature. |
| Junction temperature (Tj ) | 110 °C or Tj max - 40 °C (whichever is lower) for Si FET and SiGe bipolar transistors.  Exception :  125 °C or Tj max - 25 °C (whichever is lower) for Si, providing:  1. that the specified maximum rating Tjmax ≥ 150 °C, and  2. when life tests are performed at Tjmax.  115 °C or Tj max - 25 °C (whichever is lower) for GaAs and InP bipolar transistors.  145 °C or Tj max - 25 °C (whichever is lower) for GaN transistors  ESCC Exceptions :  (a) 125 °C for GaAs or InP, providing that:   1. the specified maximum rating Tmax ≥ 150 °C , 2. Devices or Processes are supported by ESCC 2269010 and 2265010 evaluation program or equivalent, and 3. the related evaluation reports are available.   (b) 160 °C for GaN, providing that:   1. the specified maximum rating Tjmax ≥ 200 °C , 2. the temperature junction definition is consistent with the one used for reliability demonstration, and 3. Devices or Processes are supported by ESCC 2269010 and 2265010 evaluation program or equivalent and that the related evaluation reports are available. It is important that test results include the evidence of an equivalent operation life time ≥ 20 years.   (c) 125 °C or Tj max - 25 °C (whichever is lower) for Si, providing that:   1. the specified maximum rating Tj max ≥ 150 °C , 2. when life tests are performed at Tj max, and 3. Devices or Processes are supported by ESCC 2269010 and 2265010 evaluation program or equivalent and that the related evaluation reports are available. It is important that test results include the evidence of an equivalent operation life time ≥ 20 years. |
| NOTE 1: For SI, GaAs and INP devices, when supported by reliability data, the compression level is derated to 2dB under the highest compression level showing no drift. No compression levels exceeding 1dB are applied to FETs without compression data.  NOTE 2: For GaN devices, when supported by step stress reliability data, the maximum allowed operating output power level is Pout(PAEmax). The available stress test data for varying input power levels demonstrates the achievement of at least Pout(PAEmax) +2dB without observation of any drift. Pout(PAEmax) - 3dB is the maximum allowed operating power when compression step stress data is not available.  NOTE 3: It is expected that the manufacturer datasheets use guidelines specified in IEC60134 (“Absolute maximum and design ratings of tube and semiconductor devices”) for definition of AMR and ROR ratings. | |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140142

Transistors that can be radiation sensitivshall be:

recorded in the design file, and

the components selection be reviewed and approved as specified in ECSS-Q-ST-60.

## Wires and cables - family-group code: 13-01 to 13-03

### <<deleted>>

.

### <<deleted>>Derating

ECSS-Q-ST-30-11\_0140143

<<deleted>>

ECSS-Q-ST-30-11\_0140144

<<deleted>>

ECSS-Q-ST-30-11\_0140145

<<deleted>>

ECSS-Q-ST-30-11\_0140146

Table ‑: <<deleted>>



ECSS-Q-ST-30-11\_0140147

Table ‑: <<deleted>>



### <<deleted>>

### Single wire sizing

Parameters of Wires and cables from family­group code 13­01 to 13­03 shall be rated as follows:

Voltage: 50 %

The surface temperature of the wire remains 50 °C lower than the manufacturer’s maximum rating.

The following formula may be used to rate the maximum current in a single wire (ISW), specified in requirement 6.32.4a in vacuum, for an environment temperature of Tenv environment, to reach a wire surface temperature of Twire, providing the following conditions are met:

the radial thermal gradient between wire outer surface and the inner conductor core is insignificant under nominal currents and can therefore be neglected:

Twire ≈ Tcond ≈ Tdiel

where

Twire = Effective wire temperature [K]

Tcond = Conductor temperature [K]

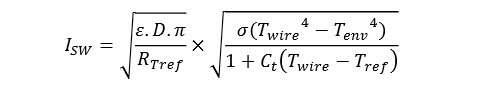
Tdiel = External temperature of the wire’s dielectric [K]

the heat transfer along the axis of the conductor can be neglected (i.e. there is no significant temperature gradient along the wire)

the dielectric is fully opaque e.g. the absorptivity equals 1

no external radiative source are present (e.g.: no solar flux), the absorptivity of the environment considered as a black body is supposed to be equal to 1

no overshields or braids are applied.



where:

ISW = Single wire current for the considered wire gauge [A]

 = Stephan-Boltzman constant = 5,67 E10-8 [W /(m2 K4)]

Twire = Effective wire temperature [K]

Tref = Reference temperature for the resistance (for example 293,15 K or 20 °C [K]

Tenv = Temperatures of the environment considered as a black body [K]

RTref = Ohmic resistance (ohm/m) at Tref (for example at 20 °C as previously considered) [Ω/m]

Ct = Coefficient of temperature for the wire resistance [K-1]

 = Thermal Emissivity of the wire’s surface [-]

D = Wire’s external diameter [m]

In case conditions specified in the requirement 6.32.4b are not fulfilled, a specific thermal analysis shall be conducted in accordance with requirements from clause 6.32.6.

1. An example of calculation with conservative values for commonly used wires is given in Annex C.

The harness designer shall make sure that the temperature of each component connected to the wire is compatible with the selected wire temperature Twire.

1. Examples of components connected to the wire are contacts, connectors, etc.

### Sizing of wires and cables in bundles

#### Fully loaded bundles

The derating on current for bundles with N wires IBW, shall be calculated as IBW = ISW × K, with ISW being the rated current for single wire and K as specified in Table 6‑41.

1. A graphically representation of Table 6‑41 is given in Figure C-1 of Annex C.

Table 6‑41: Derating factor for bundles (fully loaded)

|  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- |
| Count of wires |  | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 15 | 25 | 50 | 100 | 200 | 300 |
| Bundle derating factor |  | 1 | 0,9 | 0,81 | 0,76 | 0,71 | 0,66 | 0,62 | 0,6 | 0,59 | 0,57 | 0,49 | 0,4 | 0,29 | 0,21 | 0,15 | 0,12 |

#### Partially loaded bundles

In case of wires in cold redundancy or wires not used in the same bundle, some with current, others without current, the derating current for bundle, IBW, shall be calculated as IBW = ISW × K x L, with ISW being the rated current for single wire, K as specified in Table 6‑41, and L as specified in Table 6‑42.

Table 6‑42: Additional factor for partially loaded bundles

|  |  |  |  |
| --- | --- | --- | --- |
| Percentage of used wires | Less than 25% | Above 25% and  less than 50% | More than 50% |
| L | 1,2 | 1,1 | 1 |

### Sizing of wires and cables in bundles for specific cables or environment conditions

If the conditions specified in clause 6.32.4 are not met, or for specific cables or load conditions, a thermal simulation to validate that the surface temperature of the wire remains 50 °C lower than the manufacturer’s maximum rating shall be proposed.

The simulation specified in the requirement 6.32.6a shall include:

the radiative and conductive thermal exchanges within the bundle,

the radiative exchanges between the bundle and the environment, including possible solar fluxes,

the worst case physical parameters of the wires: minimum diameter, surface emissivity, maximum resistance at the worst case operating temperature,

application of overshields or braids if applicable.

The simulation tool and its parameters shall be validated experimentally on bundles during thermal vacuum tests.

## Opto-electronics - family-group code: 18-01 to 18-05

### General

<<deleted - moved to 6.33.3a>>

<<deleted - moved to 6.33.3b>>

<<deleted - moved to 6.33.3c>>

### Derating

ECSS-Q-ST-30-11\_0140148

Parameters of Opto-electronics from family-group code 18-01 to 18-05 shall be derated as per Table 6‑43.

ECSS-Q-ST-30-11\_0140149

Table 6‑43: Derating of parameters for Opto-electronics family-group code 18-01 to 18-05

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Light emitting diode: |  |
| Forward current | Manufacturer recommended value, or derate to 50 % if not available |
| Reverse voltage | Derate to 75 % |
| Photo transistor: |  |
| Maximum collector current | Derate to 80 % |
| Maximum collector-emitter voltage | Derate to 75 % |
| Light emitting diode and photo transistor: | |
| Junction temperature (Tj ) | 110 °C or Tj max -40 °C (whichever is lower) |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140150

Light emitting diodes that can be radiation sensitive shall be:

recorded in the design file, and

the component selection be reviewed and approved as specified in ECSS-Q-ST-60.

1. Light emitting diodes have high sensitivity to proton displacement damage.

ECSS-Q-ST-30-11\_0140151

Opto-couplers that can be radiation sensitive shall be:

recorded in the design file, and

the component selection be reviewed and approved as specified in ECSS-Q-ST-60.

1. Operation of opto-couples at low diode currents increase radiation senstitivity.

ECSS-Q-ST-30-11\_0140152

Photo-transistors that can be radiation sensitiveshall be:

recorded in the design file, and

the component selection be reviewed and approved as specified in ECSS-Q-ST-60.

## RF passive components: family-group code: 30-01, 30-07, 30-09, 30-10 and 30-99

### General

<<deleted - moved to 6.34.3a.>>

### Derating

<<Table deleted - Requirement for RF power moved to 6.34.3b>>

#### Low power < 5 W

ECSS-Q-ST-30-11\_0140153

Parameters of RF passive components from family-group code 30-01, 30-07, 30-09, 30-10 and 30-99 shall be derated for Low power < 5 W as per Table 6‑44 and for High power ≥ 5 W as per Table 6‑45.

ECSS-Q-ST-30-11\_0140154

Table 6‑44: Derating of parameters for RF passive components from family-group code 30-01, 30-07, 30-09, 30-10 and 30-99 - Low power < 5 W

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| RF power | 75 % |
| Hot spot temperature | 30 °C below maximum rated temperature. |

#### High power ≥ 5 W

ECSS-Q-ST-30-11\_0140155

Parameters of RF passive components from family-group code 30-01, 30-07, 30-09, 30-10 and 30-99 shall be derated for High power ≥ 5 W as per Table 6‑45.

ECSS-Q-ST-30-11\_0140156

Table 6‑45: Derating of parameters for RF passive components from family-group code 30-01, 30-07, 30-09, 30-10 and 30-99 - Low power ≥ 5 W

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| RF power | 75 % |
| Hot spot temperature | 5 °C below qualification temperature |

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140157

For connectorized components, connector savers shall be used during testing of equipment to minimize number of mating and demating cycles.

ECSS-Q-ST-30-11\_0140158

RF power shall be limited such that a 6 dB margin exists before the onset of multipactor.

ECSS-Q-ST-30-11\_0140159

Maximum mating and de-mating cycles shall be limited to 50 cycles.

## Fibre optic components: fibre and cable: family-group-code: 27-01

### General

<<deleted - Table moved to Table 6‑46>>

### Derating

No derating clause.

### Additional requirements not related to derating

ECSS-Q-ST-30-11\_0140160

Parameters of Fibre optic components shall be derated as per Table 6‑46.

ECSS-Q-ST-30-11\_0140161

Table 6‑46: Derating of parameters for Fibre optic components

|  |  |
| --- | --- |
| Parameters | Load ratio or limit |
| Bend radius | 200 % of the minimum value |
| Cable tension | 50 % of the rated tensile strength |
| Fibre tension | 20 % of the proof test |

## Hybrids

1. <<Requirement 6.36a. from previous issue moved to 6.36.2a>>

### General

<<No general clause>>

### Derating

ECSS-Q-ST-30-11\_0140162

For hybrids, individual components shall be in conformance with their respective derating rules.

### Additional requirements not related to derating

No additional requirement.

1. (informative)  
   Family and group codes

This annex contains an extract from the European preferred parts list (EPPL) and it lists all the parts referred to in this Standard providing their family and group codes.

| Family code | Group code | Family | Group |
| --- | --- | --- | --- |
| 01 | 01 | Capacitors | Ceramic |
| 01 | 02 | Capacitors | Ceramic Chip |
| 01 | 03 | Capacitors | Tantalum solid |
| 01 | 04 | Capacitors | Tantalum non-solid |
| 01 | 05 | Capacitors | Plastic metallized |
| 01 | 06 | Capacitors | Glass |
| 01 | 07 | Capacitors | Mica and reconstituted mica |
| 01 | 10 | Capacitors | Feedthrough |
| 01 | 11 | Capacitors | Semiconductor |
| 01 | 99 | Capacitors | Miscellaneous |
|  | | | |
| 02 | 01 | Connectors | Circular |
| 02 | 02 | Connectors | Rectangular |
| 02 | 03 | Connectors | Printed circuit board |
| 02 | 07 | Connectors | Microminiature |
| 02 | 09 | Connectors | Rack and panel |
|  | | | |
| 03 | 01 | Piezo-electric devices | Crystal resonator |
|  | | | |
| 04 | 01 | Diodes | Switching |
| 04 | 02 | Diodes | Rectifier |
| 04 | 03 | Diodes | Voltage regulator |
| 04 | 04 | Diodes | Voltage reference/zener |
| 04 | 05 | Diodes | RF/microwave Schottky - Si |
| 04 | 06 | Diodes | Pin |
| 04 | 08 | Diodes | Transient suppression |
| 04 | 10 | Diodes | High voltage rectifier |
| 04 | 11 | Diodes | Microwave varactor - GaAs |
| 04 | 12 | Diodes | Step recovery |
| 04 | 13 | Diodes | Microwave varactor - Si |
| 04 | 14 | Diodes | Current regulator |
| 04 | 15 | Diodes | Microwave Schottky - GaAs |
| 04 | 16 | Diodes | RF/microwave - PIN |
| 04 | 17 | Diodes | Microwave Gunn - GaAs |
|  | | | |
| 05 | 01 | Filters | Feedthrough |
|  | | | |
| 06 | 01 | Fuses | All |
|  | | | |
| 07 | 01 | Inductors | RF coil |
| 07 | 02 | Inductors | Cores |
| 07 | 03 | Inductors | Chip |
|  | | | |
| 08 | 10 | Microcircuits | Microprocessors/microcontrollers/ peripherals |
| 08 | 20 | Microcircuits | Memory SRAM |
| 08 | 21 | Microcircuits | Memory DRAM |
| 08 | 22 | Microcircuits | Memory PROM |
| 08 | 23 | Microcircuits | Memory EPROM |
| 08 | 24 | Microcircuits | Memory EEPROM |
| 08 | 29 | Microcircuits | Memory others |
| 08 | 30 | Microcircuits | Programmable logic |
| 08 | 40 | Microcircuits | ASIC technologies digital |
| 08 | 41 | Microcircuits | ASIC technologies linear |
| 08 | 42 | Microcircuits | ASIC technologies mixed analogue/digital |
| 08 | 50 | Microcircuits | Linear operational amplifier |
| 08 | 51 | Microcircuits | Linear sample and hold amplifier |
| 08 | 52 | Microcircuits | Linear voltage regulator |
| 08 | 53 | Microcircuits | Linear voltage comparator |
| 08 | 54 | Microcircuits | Linear switching regulator |
| 08 | 55 | Microcircuits | Linear line driver |
| 08 | 56 | Microcircuits | Linear line receiver |
| 08 | 57 | Microcircuits | Linear timer |
| 08 | 58 | Microcircuits | Linear multiplier |
| 08 | 59 | Microcircuits | Linear switches |
| 08 | 60 | Microcircuits | Linear multiplexer/demultiplexer |
| 08 | 61 | Microcircuits | Linear analog to digital converter |
| 08 | 62 | Microcircuits | Linear digital to analogue converter |
| 08 | 69 | Microcircuits | Linear other functions |
| 08 | 80 | Microcircuits | Logic families |
| 08 | 95 | Microcircuits | MMIC |
| 08 | 99 | Microcircuits | Miscellaneous |
|  | | | |
| 09 | 01 | Relays | Non-latching |
| 09 | 02 | Relays | Latching |
|  | | | |
| 10 | 01 | Resistors | Metal oxide |
| 10 | 02 | Resistors | Wire-wound precision - including surface mount |
| 10 | 03 | Resistors | Wire-wound chassis mounted |
| 10 | 04 | Resistors | Variable trimmers |
| 10 | 05 | Resistors | Composition |
| 10 | 07 | Resistors | Shunt |
| 10 | 08 | Resistors | Metal film |
| 10 | 09 | Resistors | Chip - all |
| 10 | 10 | Resistors | Network - all |
| 10 | 11 | Resistors | Heaters, flexible |
|  | | | |
| 11 | 01 | Thermistors | Temperature compensating |
| 11 | 02 | Thermistors | Temperature measuring |
| 11 | 03 | Thermistors | Temperature sensor |
|  | | | |
| 12 | 01 | Transistors | Low power, NPN - < 2 W |
| 12 | 02 | Transistors | Low power, PNP - < 2 W |
| 12 | 03 | Transistors | High power, NPN - > 2 W |
| 12 | 04 | Transistors | High power, PNP - > 2 W |
| 12 | 05 | Transistors | FET N channel |
| 12 | 06 | Transistors | FET P channel |
| 12 | 09 | Transistors | Switching |
| 12 | 10 | Transistors | RF/microwave NPN low power/low noise |
| 12 | 12 | Transistors | RF/microwave  FET N-channel/P-channel |
| 12 | 13 | Transistors | RF/microwave bipolar power |
| 12 | 14 | Transistors | RF/microwave FET power - Si |
| 12 | 15 | Transistors | Microwave power - GaAs |
| 12 | 16 | Transistors | Microwave low noise - GaAs |
|  | | | |
| 13 | 01 | Wires and cables | Low frequency |
| 13 | 02 | Wires and cables | Coaxial |
| 13 | 03 | Wires and cables | Fibre optic |
|  | | | |
| 14 | 01 | Transformers | Power |
|  | | | |
| 16 | 01 | Switches | Standard DC/AC power toggle |
| 18 | 01 | Opto-electronics | Opto-coupler |
| 18 | 02 | Opto-electronics | LED |
| 18 | 03 | Opto-electronics | Phototransistor |
| 18 | 04 | Opto-electronics | Photo diode/sensor |
| 18 | 05 | Opto-electronics | Laser diode |
|  | | | |
| 27 | 01 | Fibreoptic components | Fibre/cable |
|  | | | |
| 30 | 01 | RF passive devices | Coaxial couplers |
| 30 | 07 | RF passive devices | Isolator/circulator |
| 30 | 09 | RF passive devices | Coaxial power dividers |
| 30 | 10 | RF passive devices | Coaxial attenuators/loads |
| 30 | 99 | RF passive devices | Miscellaneous |

1. (informative)  
   ESCC Exceptions

This annex contains the list of the ESCC detail specifications applicable at the time of publication and containing deviations to general derating requirements of this standard.

There are presently no ESCC Detail Specifications recording derating deviations to ECSS-Q-ST-30-11.

1. (informative)  
   Example of single wires rating currents calculation for the wires most commonly used for space applications
   1. Introduction

All of the values given in this Annex are for information: it’s the designer’s responsibility to assess the values of the parameters for the type of wires and cables that have been selected.

* 1. Typical conservative parameters
* Emissivity of the wire surface: E = 0,75.
* Coefficient of temperature for the wire resistance:

Ct = 0,00396 K­1 for copper

Ct = 0,004 K­1 for aluminum wires.

The above values are given for: Tref = 293,15 K.

As an example, the tables here after give a set of physical parameter values for each gauge of wire which are conservative for most of the cables covered by the ESCC 3901/xxx. The minimum value of the diameter is considered because it represents the worst case as it minimizes the radiative surface of the wire, and therefore its cooling capability.

: Parameters for Copper and Copper Alloy wires

|  |  |  |  |  |  |  |  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- | --- |
| Wire Size (AWG) | 28 | 26 | 24 | 22 | 20 | 18 | 16 | 14 | 12 | 10 | 8 | 4 | 0 |
| Resistance at 20°C (mOhm/m) | 242 | 148 | 105 | 50,9 | 32,2 | 20,6 | 14,3 | 10,1 | 6,03 | 3,9 | 2,38 | 0,91 | 0,38 |
| Min diameter (mm) | 0,6 | 0,7 | 0,8 | 1 | 1,2 | 1,45 | 1,77 | 2,07 | 2,68 | (\*) | (\*) | (\*) | (\*) |
| (\*) Gauges not available in ESCC3901 | | | | | | | | | | | | | |

: Parameters for Aluminum wires

|  |  |  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- | --- | --- |
| Wire Size (AWG) | 22 | 20 | 18 | 16 | 14 | 12 | 10 | 8 |
| Resistance at 20°C (mOhm/m) | 92 | 52 | 33 | 23 | 17 | 10,3 | 6,4 | 3,6 |
| Min diameter (mm) | 0,88 | 1,13 | 1,38 | 1,73 | 2,1 | 2,7 | 3,45 | 4,85 |

* 1. Example of current rating values for single wires

The values in Table C-3, Table C-4were calculated using the above formula and list of parameters, for an environment temperature of 70 °C.

Copper wires:

Maximum wire temperature: 150°C

: Single wire rated current for a copper conductor for the parameter values of Table C-1

|  |  |  |  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- | --- | --- | --- |
| Wire Size (AWG) | 28 | 26 | 24 | 22 | 20 | 18 | 16 | 14 | 12 |
| Rated current (A) ISW | 1,9 | 2,7 | 3,4 | 5,6 | 7,7 | 10,6 | 14 | 18,1 | 26,7 |

Aluminum wires:

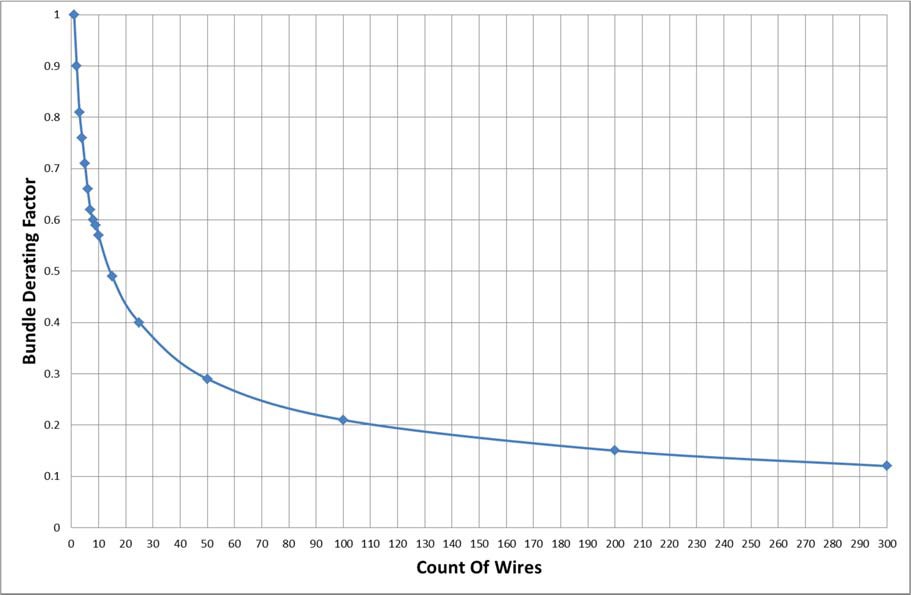
Maximum wire temperature: 100 °C

: Single wire rated current for an aluminum conductor for parameter values of Table C-2

|  |  |  |  |  |  |  |  |  |
| --- | --- | --- | --- | --- | --- | --- | --- | --- |
| Wire Size (AWG) | 22 | 20 | 18 | 16 | 14 | 12 | 10 | 8 |
| Rated current (A) ISW | 2,3 | 3,4 | 4,8 | 6,4 | 8,3 | 12,1 | 17,3 | 27,4 |

* 1. Chart of Derating Factor K for Fully Loaded Bundles

Figure C-1 is a graphical representation of the table provided in Table 6‑41.



: Derating factor for fully loaded bundle

Bibliography

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| --- | --- |
| ECSS-S-ST-00 | ECSS system - Description and implementation and general requirements |